



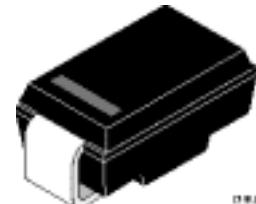
# Schottky Diode (FH1N5819)

肖特基二极管

## Features 特征:

- Ideal for surface mounted applications
- Low leakage current.
- For use in low voltage, high frequency inverters free wheeling, and polarity protection applications.

DO-214AC



## 1.0Ampere Schottky Barrier Rectifiers

### 1.0 安培肖特基势垒整流二极管

#### Absolute Maximum Ratings\* 最大绝对值

T<sub>A</sub>=25 unless otherwise noted

Symbol 符号	Parameter 参数	Value	Units
I <sub>F(AV)</sub>	Average Rectified Current 平均整流电流	1.0	A
I <sub>FSM</sub>	Non-repetitive Peak Forward Surge Current 无重复正向峰值浪涌电流 8.3 ms single half-sine-wave superimposed on rated load	30	A
P <sub>D</sub>	Total Device Dissipation 总耗散功率 Derate above 25	1.25 12.5	W MW/
R <sub>JA</sub>	Thermal Resistance, Junction to Ambient 热阻	20	/W
T <sub>STG</sub>	Storage Temperature Range 储存温度	-65 to +150	
T <sub>J</sub>	Operating Junction Temperature 工作结温	-65 to +150	

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### Electrical Characteristics T<sub>A</sub>=25 unless otherwise noted

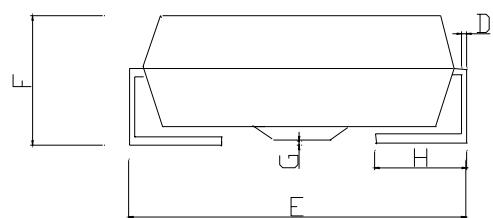
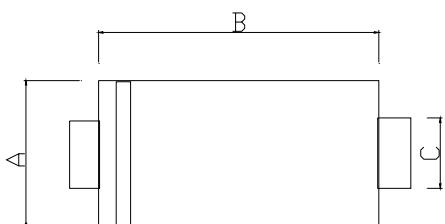
Symbol 符号	Parameter 参数	Value	Units
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage 最大峰值反向电压	40	V
V <sub>RMS</sub>	Maximum RMS Voltage	28	V
V <sub>R</sub>	DC Reverse Voltage (Rated V <sub>R</sub> ) 反向电压	40	V
I <sub>RM</sub>	Maximum Instantaneous Reverse Current 最大瞬间反向电流 T <sub>A</sub> =25 @rated V <sub>R</sub> T <sub>A</sub> =100	0.5 10	mA mA
V <sub>FM</sub>	Maximum Instantaneous Forward Voltage 最大瞬间正向电压 @1.0A	500	mV
C	Typical Junction capacitance 典型结容	110	pF



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## DO-214AC Dimensions in INCHES(MILLIMETERS)

### DO - 214AC 尺寸 英寸(毫米)



	A	B	C	D
MAX	0.110(2.79)	0.177(4.50)	0.075(1.90)	0.012(0.305)
MIN	0.100(2.54)	0.157(3.99)	0.052(1.32)	0.006(0.152)
	E	F	G	H
MAX	0.208(5.28)	0.90(2.29)	0.008(0.203)	0.060(1.52)
MIN	0.194(4.93)	0.078(1.98)	0.004(0.102)	0.030(0.76)